

NSS30070MR6T1G

30 V, 0.7 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- This Device is Pb-Free and is RoHS Compliant

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Collector-Base Voltage	V_{CBO}	40	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	700	mA
Base Current	I_B	350	mA
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	342	mW
Total Power Dissipation @ $T_C = 85^\circ\text{C}$	P_D	178	mW
Thermal Resistance - Junction-to-Ambient (Note 1)	$R_{\theta JA}$	366	$^\circ\text{C}/\text{W}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	665	mW
Total Power Dissipation @ $T_C = 85^\circ\text{C}$	P_D	346	mW
Thermal Resistance - Junction-to-Ambient (Note 2)	$R_{\theta JA}$	188	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

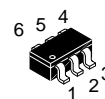
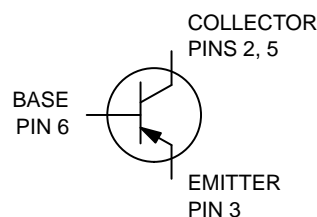
1. Minimum FR-4 or G-10 PCB, Operating to Steady State.
2. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), Operating to Steady State.



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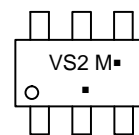
<http://onsemi.com>

30 VOLTS
0.7 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 320 mΩ



SC-74
CASE 318F
STYLE 2

DEVICE MARKING



VS2 = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NSS30070MR6T1G	SC-74 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSS30070MR6T1G

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage (I _C = 100 μA)	V _{(BR)CBO}	40	-	-	V
Collector-Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	30	-	-	V
Emitter-Base Breakdown Voltage (I _E = 100 μA)	V _{(BR)EBO}	5.0	-	-	V
Collector Cutoff Current (V _{CB} = 25 V, I _E = 0 A) (V _{CB} = 25 V, I _E = 0 A, T _A = 125°C)	I _{CBO}	-	-	1.0 10	μA
Emitter Cutoff Current (V _{EB} = 5.0 V, I _C = 0 A)	I _{EBO}	-	-	10	μA
ON CHARACTERISTICS					
DC Current Gain (V _{CE} = 3.0 V, I _C = 100 mA)	h _{FE}	150	-	-	V
Collector-Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}	-	-	0.25	V
Collector-Emitter Saturation Voltage (I _C = 700 mA, I _B = 70 mA)	V _{CE(sat)}	-	-	0.4	V
Base-Emitter Saturation Voltage (I _C = 700 mA, I _B = 70 mA)	V _{BE(sat)}	-	-	1.1	V
Base-Emitter Turn-On Voltage (I _C = 700 mA, V _{CE} = 1.0 V)	V _{BE(on)}	-	-	1.0	V

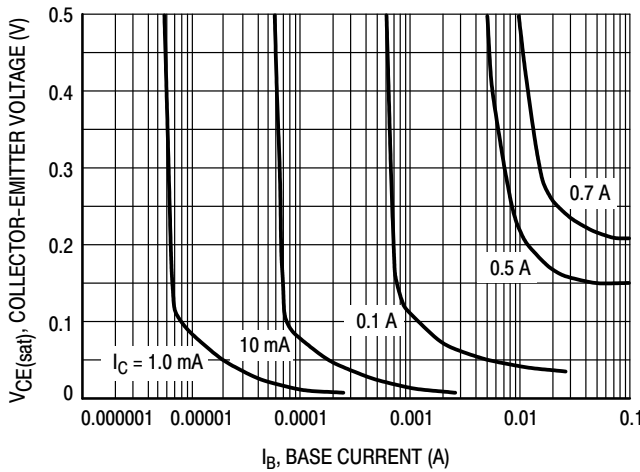


Figure 1. Collector Saturation Region

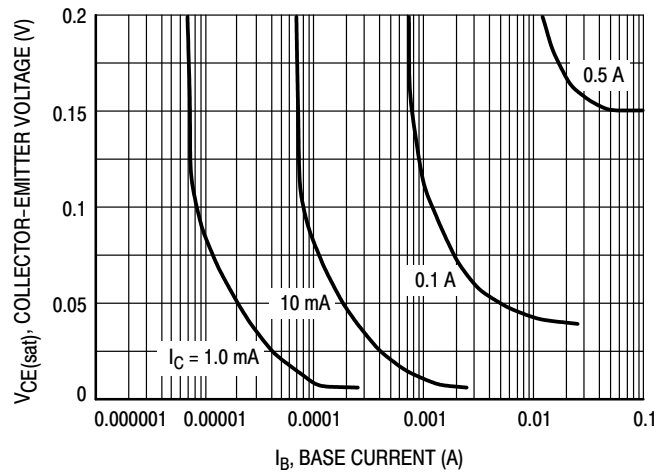


Figure 2. Collector Saturation Region

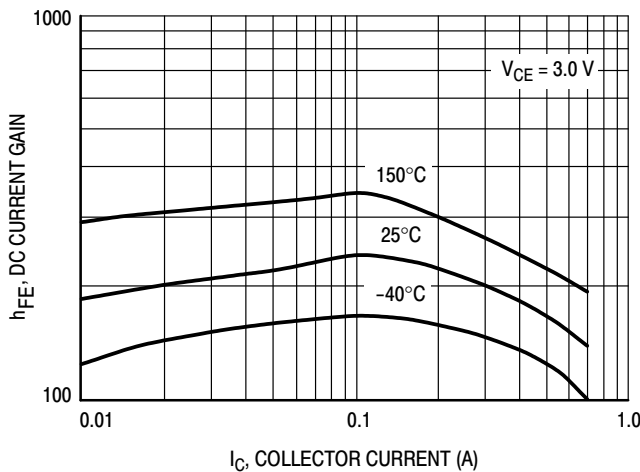


Figure 3. DC Current Gain

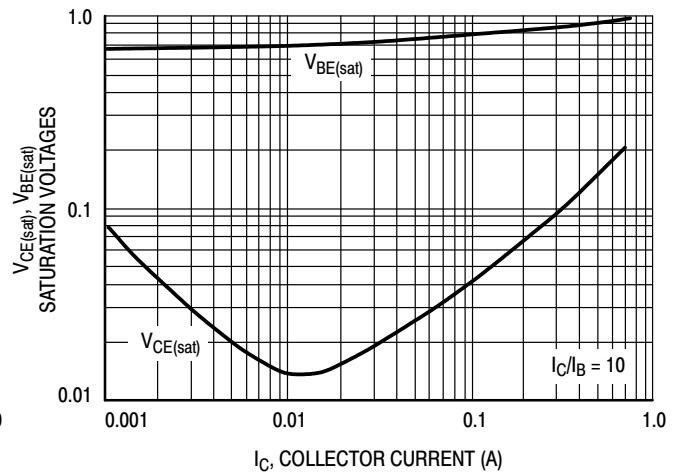


Figure 4. "SAT" Voltages

NSS30070MR6T1G

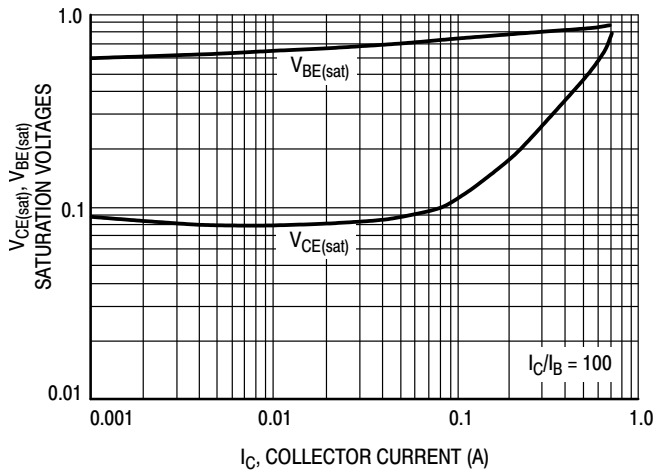


Figure 5. "SAT" Voltages

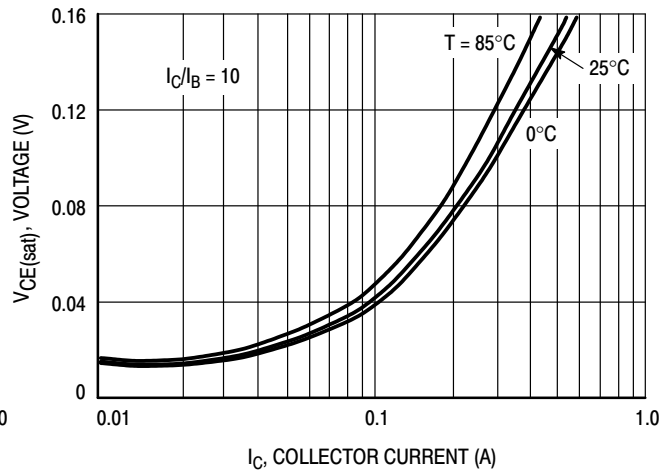


Figure 6. Collector-Emitter Saturation Voltage

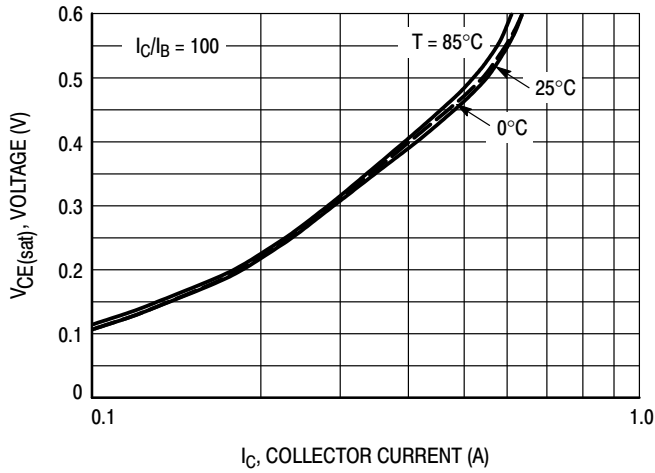


Figure 7. Collector-Emitter Saturation Voltage

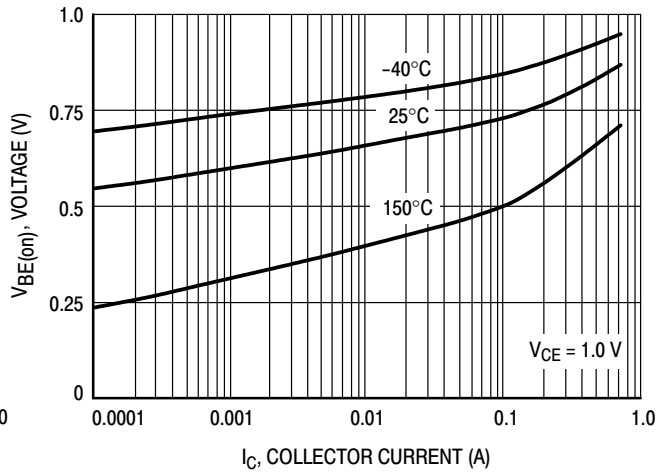


Figure 8. $V_{BE(on)}$ Voltage

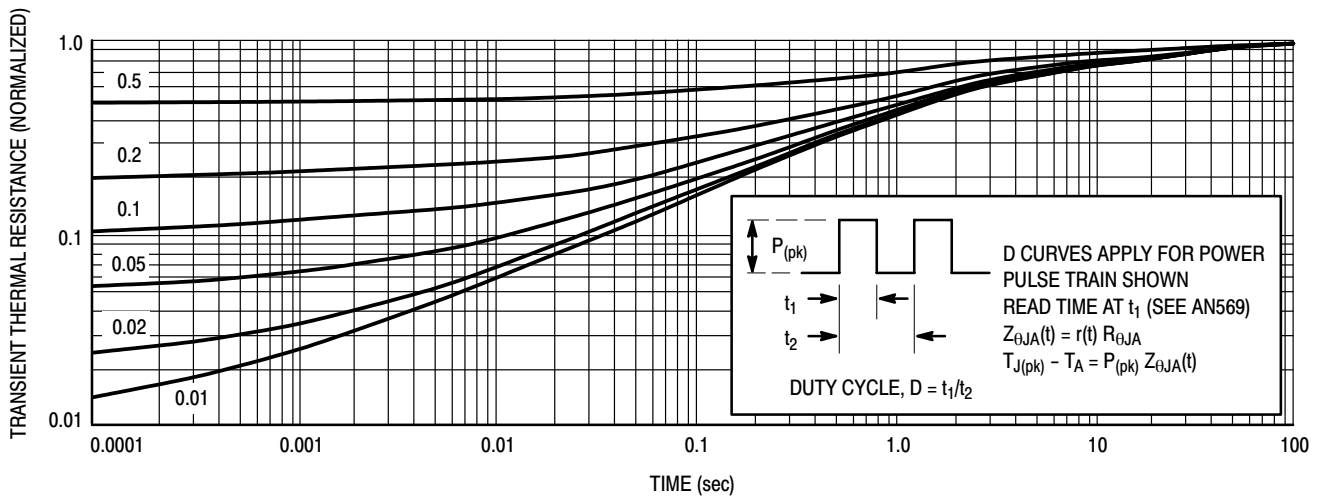


Figure 9. Thermal Response Curve

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 2:1

SC-74
CASE 318F
ISSUE P

DATE 07 OCT 2021

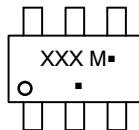


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
HE	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0*	---	10*	0*	---	10*

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

- | | | | | | |
|--|---|--|---|--|--|
| <p>STYLE 1:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE</p> | <p>STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE</p> | <p>STYLE 3:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1</p> | <p>STYLE 4:
PIN 1. COLLECTOR 2
2. EMITTER 1/EMITTER 2
3. COLLECTOR 1
4. EMITTER 3
5. BASE 1/BASE 2/COLLECTOR 3
6. BASE 3</p> | <p>STYLE 5:
PIN 1. CHANNEL 1
2. ANODE
3. CHANNEL 2
4. CHANNEL 3
5. CATHODE
6. CHANNEL 4</p> | <p>STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE</p> |
| <p>STYLE 7:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1</p> | <p>STYLE 8:
PIN 1. EMITTER 1
2. BASE 2
3. COLLECTOR 2
4. EMITTER 2
5. BASE 1
6. COLLECTOR 1</p> | <p>STYLE 9:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2</p> | <p>STYLE 10:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE</p> | <p>STYLE 11:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR</p> | |

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